# SQ4946AEY



Vishay Siliconix

# Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	60			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.040			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 4.5 V	0.055			
I <sub>D</sub> (A) per leg	7			
Configuration	Dual			

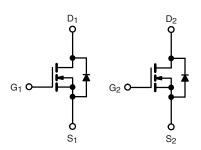


#### **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- 100 % R<sub>g</sub> and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



FREE



N-Channel MOSFET N-Channel MOSFET

ORDERING INFORMATION					
Package	SO-8				
Lead (Pb)-free and Halogen-free	SQ4946AEY-T1-GE3				

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	60	V		
Gate-Source Voltage		V <sub>GS</sub> ± 20		V		
Continuous Drain Current	T <sub>C</sub> = 25 °C	I	7			
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	4			
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	3.6	А		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	28			
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	18			
Single Pulse Avalanche Energy	L = 0.1 MH	E <sub>AS</sub>	16.2	mJ		
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	4	W		
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	1.3	vv		
Operating Junction and Storage Temperatur	re Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	110	°C/W	
Junction-to-Foot (Drain)		R <sub>thJF</sub>	34	0/10	

#### Notes

a. Package limited.

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

c. When mounted on 1" square PCB (FR4 material).

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	<u>.</u>	·					
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$		60	-	-	v
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		1.5	2.0	2.5	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	
		$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 \text{ V}$	$V_{DS} \ge 5 V$	20	-	-	А
		$V_{GS} = 10 V$	I <sub>D</sub> = 4.5 A	-	0.033	0.040	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 V$	I <sub>D</sub> = 4.5 A, T <sub>J</sub> = 125 °C	-	-	0.066	Ω
	- D3(01)	$V_{GS} = 10 V$	I <sub>D</sub> = 4.5 A, T <sub>J</sub> = 175 °C	-	-	0.081	
		$V_{GS} = 4.5 V$	$I_D = 4 A$	-	0.045	0.055	
Forward Transconductance f	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 4.5 \text{ A}$		-	15	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	-	600	750	pF
Output Capacitance	Coss	$V_{GS} = 0 V$		-	110	140	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	50	62	
Total Gate Charge <sup>c</sup>	Qg			-	11.7	18	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 V$	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 5.3 \text{ A}$	-	1.8	2.7	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	2.8	4.2	1
Gate Resistance	Rg	f = 1 MHz		1.3	-	6	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}}=30 \ \text{V}, \ R_{\text{L}}=6.8 \ \Omega \\ \\ I_{\text{D}}\cong4.4 \ \text{A}, \ V_{\text{GEN}}=10 \ \text{V}, \ R_{\text{g}}=1 \ \Omega \end{array}$		-	7	11	
Rise Time <sup>c</sup>	t <sub>r</sub>			-	3.3	5	- ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	22.4	33.5	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	2.1	3.2	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>	<u> </u>					
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	28	Α
Forward Voltage	V <sub>SD</sub>	$I_{\rm F} = 2 \text{ A}, V_{\rm GS} = 0 \text{ V}$		-	0.75	1.1	V

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

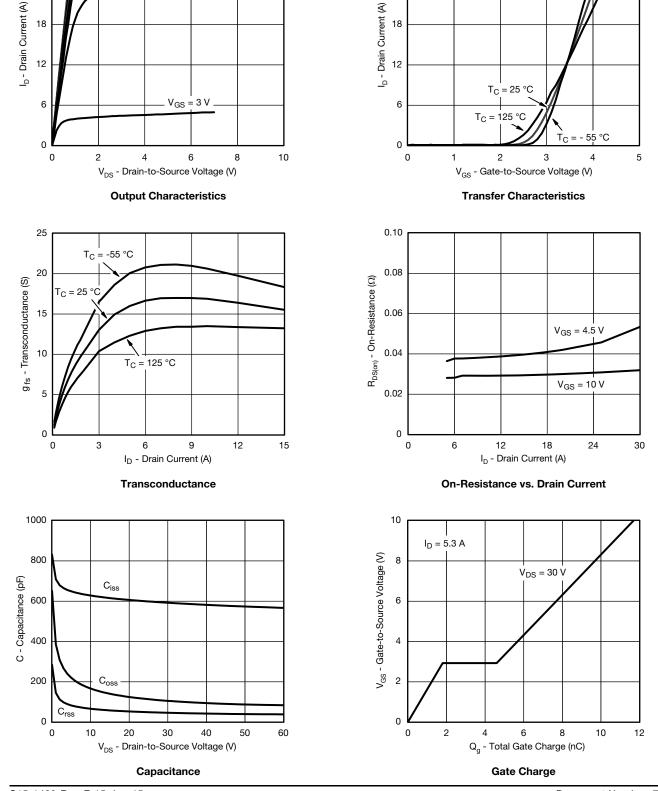
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30

24

18

12



S15-1462-Rev. F, 15-Jun-15

3 For technical questions, contact: automostechsupport@vishay.com Document Number: 71506

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## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

V<sub>GS</sub> = 10 V thru 5 V  $V_{GS} = 4 V$ 

30

24

18

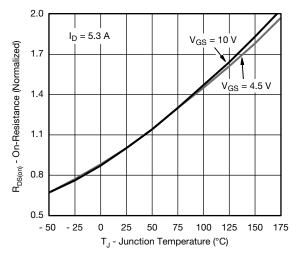
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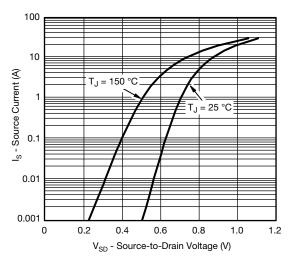
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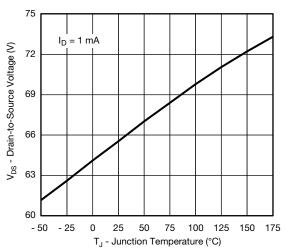
## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



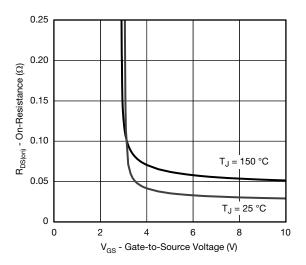
**On-Resistance vs. Junction Temperature** 



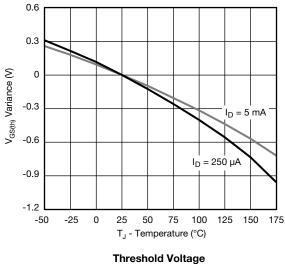
Source Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature



**On-Resistance vs. Gate-to-Source Voltage** 



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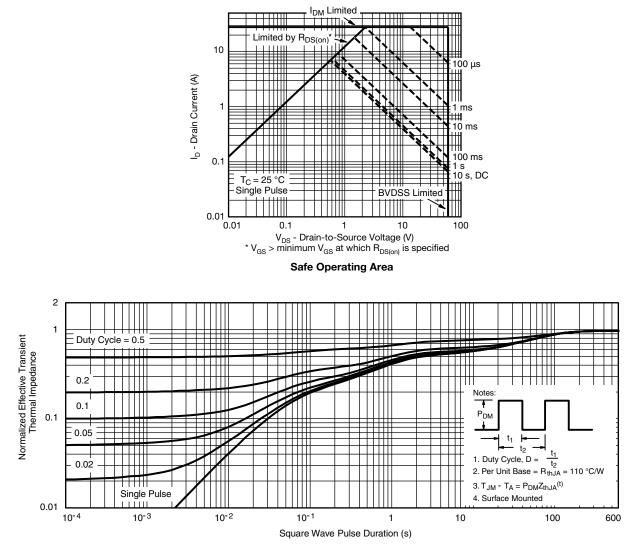
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## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

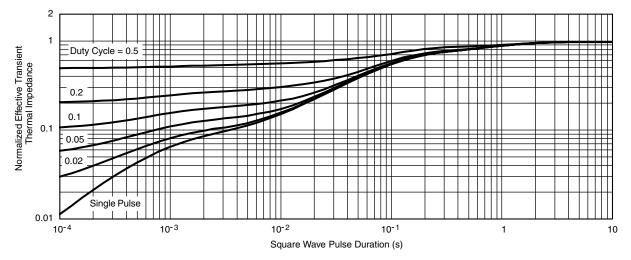


Normalized Thermal Transient Impedance, Junction-to-Ambient



## **Vishay Siliconix**

## **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

· The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?71506">www.vishay.com/ppg?71506</a>.



# Package Information

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# SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIM	IETERS	INCHES		
DIM	Min	Мах	Min	Max	
A	1.35	1.75	0.053	0.069	
A <sub>1</sub>	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498					

# **Application Note 826**

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**RECOMMENDED MINIMUM PADS FOR SO-8** 



Recommended Minimum Pads Dimensions in Inches/(mm)

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